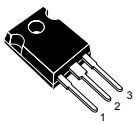
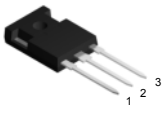
STGW40M120DF3, STGWA40M120DF3

Datasheet

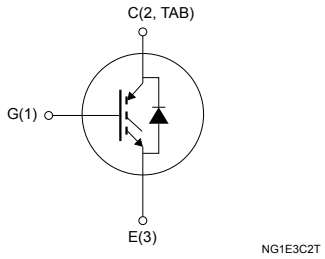
Trench gate field-stop 1200 V, 40 A low-loss M series IGBT in a TO-247 and TO-247 long leads packages



TO-247



TO-247 long leads



Features

- Maximum junction temperature: T_J = 175 °C
- 10 µs of minimum short-circuit withstand time
- $V_{CE(sat)}$ = 1.85 V (typ.) @ I_C = 40 A
- Tight parameter distribution
- Safer paralleling
- Positive $V_{CE(sat)}$ temperature coefficient
- Low thermal resistance
- Soft and very fast-recovery antiparallel diode

Applications

- Industrial drives
- Uninterruptable power supplies (UPS)
- Solar inverters
- Welding

Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. The devices are part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where the low-loss and the short-circuit functionality are essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and the tight parameter distribution result in safer paralleling operation.

Product status links
STGW40M120DF3
STGWA40M120DF3

Product summary	
Order code	**STGW40M120DF3**
Marking	G40M120DF3
Package	TO-247
Packing	Tube
Order code	**STGWA40M120DF3**
Marking	G40M120DF3
Package	TO-247 long leads
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0 V)	1200	V
I_C	Continuous collector current at T_C = 25 °C	80	A
	Continuous collector current at T_C = 100 °C	40	A
I_{CP} (1)	Pulsed collector current	160	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Continuous forward current at T_C = 25 °C	80	A
I_F	Continuous forward current at T_C = 100 °C	40	A
I_{FP}(1)	Pulsed forward current	160	A
P_{TOT}	Total power dissipation at T_C = 25 °C	468	W
T_{STG}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range	-55 to 175	°C

1. *Pulse width limited by maximum junction temperature.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case IGBT	0.32	°C/W
	Thermal resistance, junction-to-case diode	0.74	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	50	°C/W

2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	V_{GE} = 0 V, I_C = 2 mA	1200			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE} = 15 V, I_C = 40 A		1.85	2.3	V
		V_{GE} = 15 V, I_C = 40 A, T_J = 125 °C		2.2		
		V_{GE} = 15 V, I_C = 40 A, T_J = 175 °C		2.3		
V_F	Forward on-voltage	I_F = 40 A		2.85	3.95	V
		I_F = 40 A, T_J = 125 °C		2.25		
		I_F = 40 A, T_J = 175 °C		2.1		
$V_{GE(th)}$	Gate threshold voltage	V_{CE} = V_{GE}, I_C = 2 mA	5	6	7	V
I_{CES}	Collector cut-off current	V_{GE} = 0 V, V_{CE} = 1200 V			25	µA
I_{GES}	Gate-emitter leakage current	V_{GE} = ±20 V, V_{CE} = 0 V			±250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	V_{CE} = 25 V, f = 1 MHz, V_{GE} = 0 V	-	2500	-	pF
C_{oes}	Output capacitance		-	275	-	
C_{res}	Reverse transfer capacitance		-	95	-	
Q_g	Total gate charge	V_{CC} = 960 V, I_C = 40 A, V_{GE} = 0 to 15 V (see Figure 29)	-	125	-	nC
Q_{ge}	Gate-emitter charge		-	15	-	
Q_{gc}	Gate-collector charge		-	75	-	

Table 5. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V, R_G = 10 Ω (see Figure 28)		35	-	ns
t_r	Current rise time			15	-	ns
$(di/dt)_{on}$	Turn-on current slope			2100	-	A/µs
$t_{d(off)}$	Turn-off-delay time			140	-	ns
t_f	Current fall time			135	-	ns
E_{on} (1)	Turn-on switching energy			1.5	-	mJ
E_{off} (2)	Turn-off switching energy			2.25	-	mJ
E_{ts}	Total switching energy			3.75	-	mJ
$t_{d(on)}$	Turn-on delay time	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V, R_G = 10 Ω, T_J = 175 °C (see Figure 28)		35	-	ns
t_r	Current rise time			18	-	ns
$(di/dt)_{on}$	Turn-on current slope			1800	-	A/µs
$t_{d(off)}$	Turn-off-delay time			150	-	ns
t_f	Current fall time			240	-	ns
E_{on} (1)	Turn-on switching energy			2.8	-	mJ
E_{off} (2)	Turn-off switching energy			3.45	-	mJ
E_{ts}	Total switching energy			6.25	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CC} \leq$ 600 V, V_{GE} = 15 V, $T_{Jstart} \leq$ 150 °C	10		-	µs

1. *Including the reverse recovery of the diode*
2. *Including the tail of the collector current*

Table 6. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	I_F = 40 A, V_R = 600 V, V_{GE} = 15 V (di/dt = 1000 A/µs) (see Figure 28)	-	355	-	ns
Q_{rr}	Reverse recovery charge		-	2575	-	nC
I_{rrm}	Reverse recovery current		-	25	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	1110	-	A/µs
E_{rr}	Reverse recovery energy		-	1.12	-	mJ
t_{rr}	Reverse recovery time	I_F = 40 A, V_R = 600 V, V_{GE} = 15 V, T_J = 175 °C, (see Figure 28)	-	667	-	ns
Q_{rr}	Reverse recovery charge		-	8500	-	nC
I_{rrm}	Reverse recovery current		-	37	-	A
dI_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	450	-	A/µs
E_{rr}	Reverse recovery energy		-	3.9	-	mJ

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

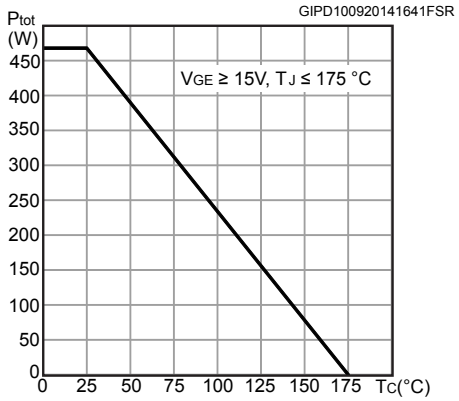


Figure 2. Collector current vs case temperature

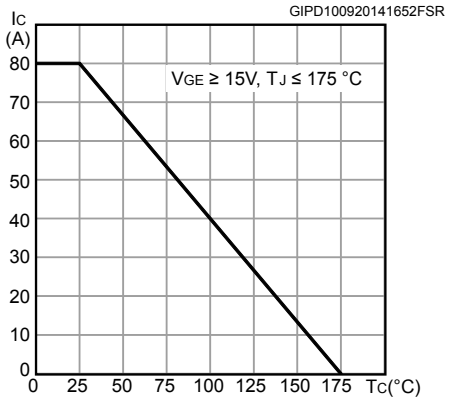


Figure 3. Output characteristics (T_J = 25 °C)

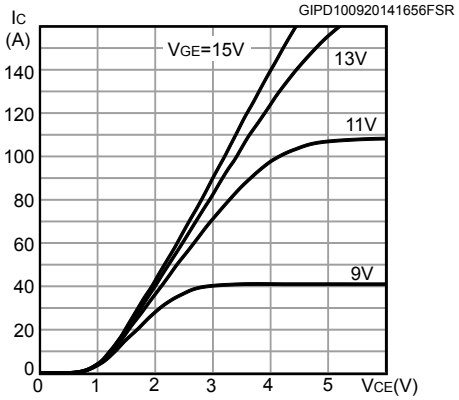


Figure 4. Output characteristics (T_J = 175 °C)

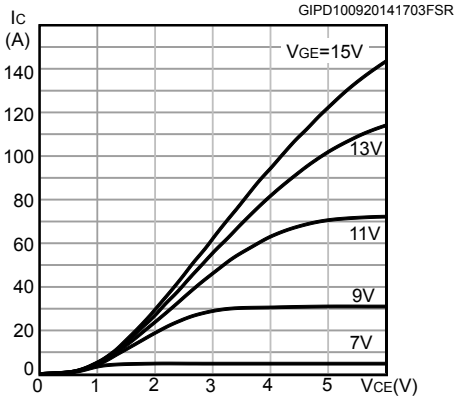


Figure 5. $V_{CE(sat)}$ vs junction temperature

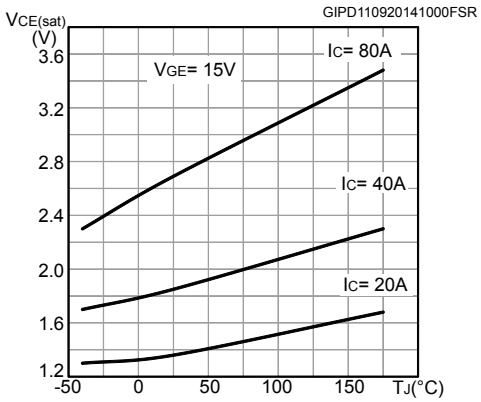


Figure 6. $V_{CE(sat)}$ vs collector current

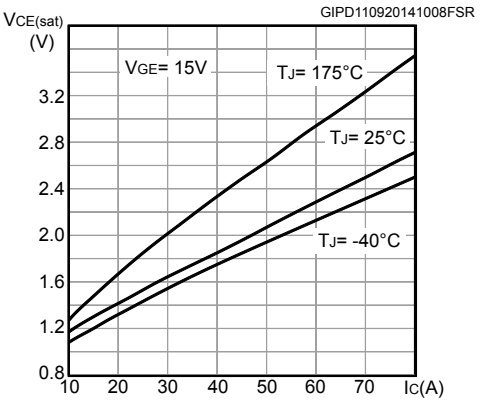


Figure 7. Collector current vs switching frequency

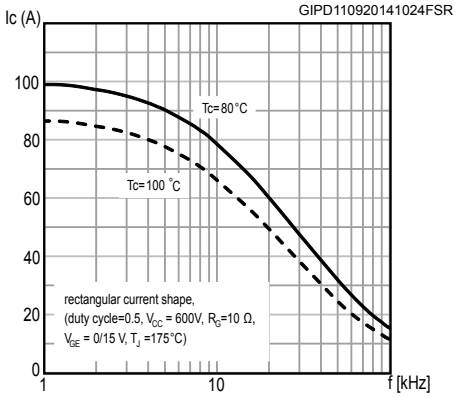


Figure 8. Forward bias safe operating area

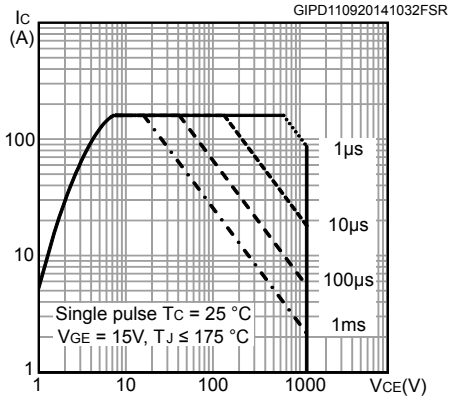


Figure 9. Transfer characteristics

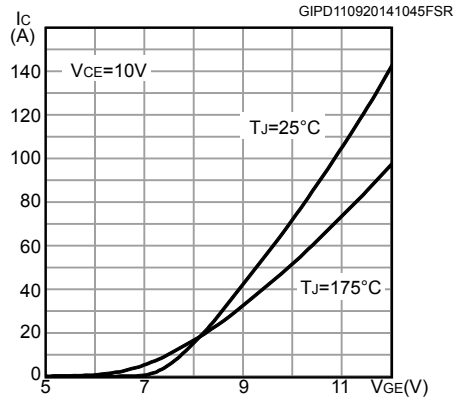


Figure 10. Diode V_F vs forward current

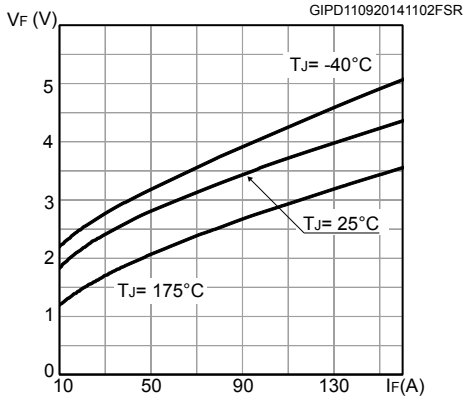


Figure 11. Normalized $V_{GE(th)}$ vs junction temperature

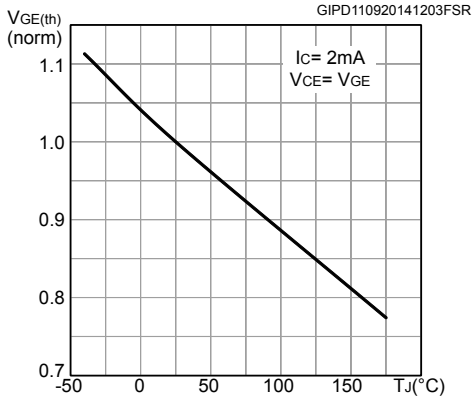


Figure 12. Normalized $V_{(BR)CES}$ vs junction temperature

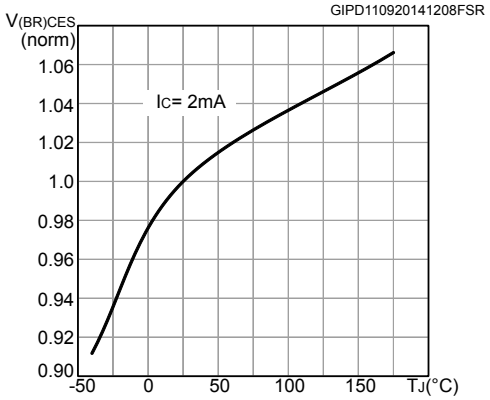


Figure 13. Capacitance variations

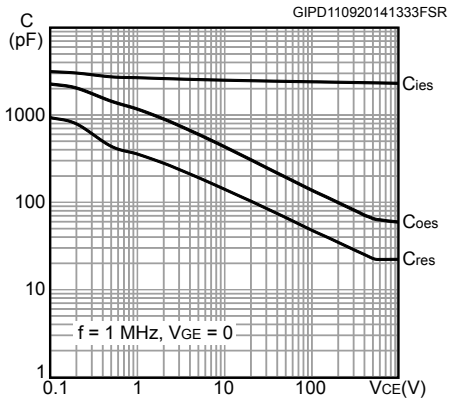


Figure 14. Gate charge vs gate-emitter voltage

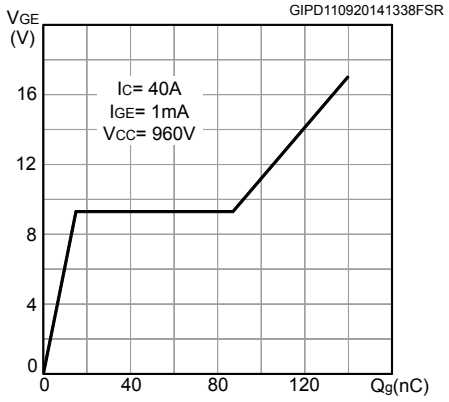


Figure 15. Switching loss vs collector current

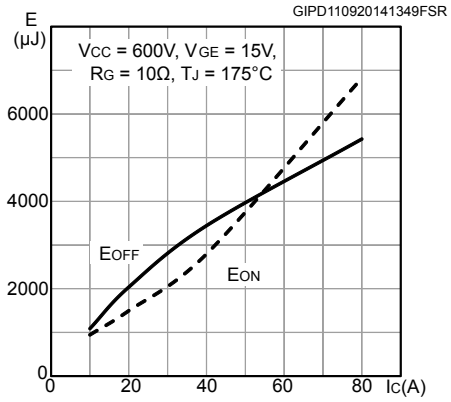


Figure 16. Switching loss vs gate resistance

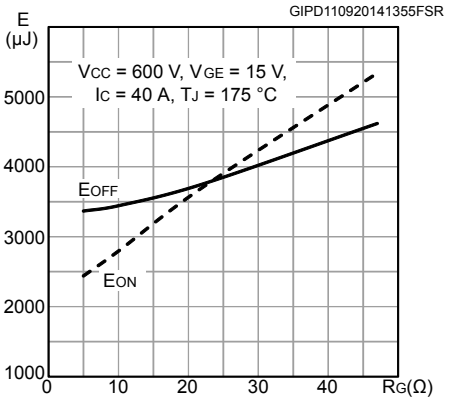


Figure 17. Switching loss vs temperature

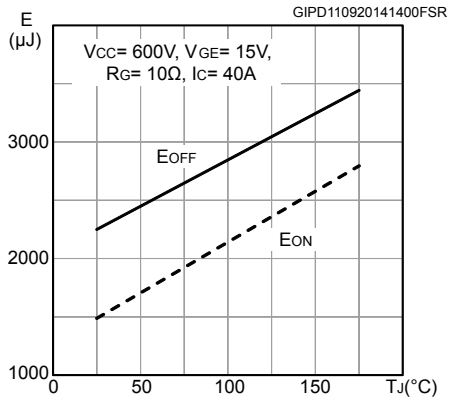


Figure 18. Switching loss vs collector emitter voltage

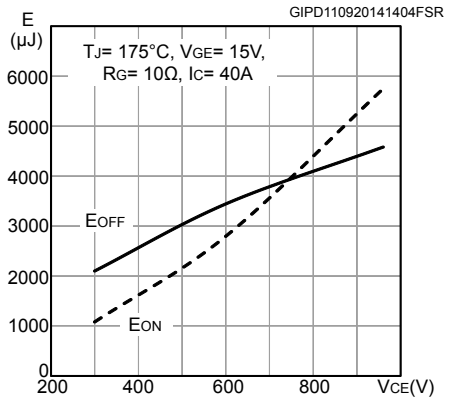


Figure 19. Short-circuit time and current vs V_{GE}

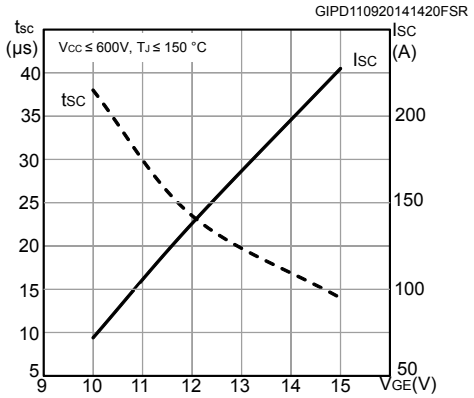


Figure 20. Switching times vs collector current

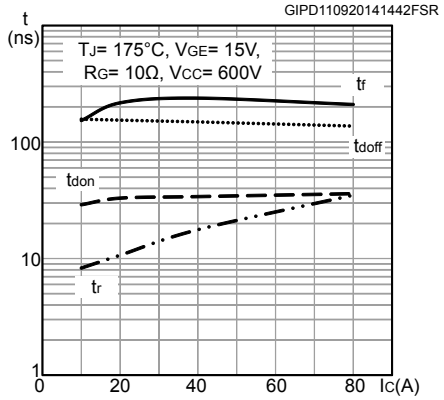


Figure 21. Switching times vs gate resistance

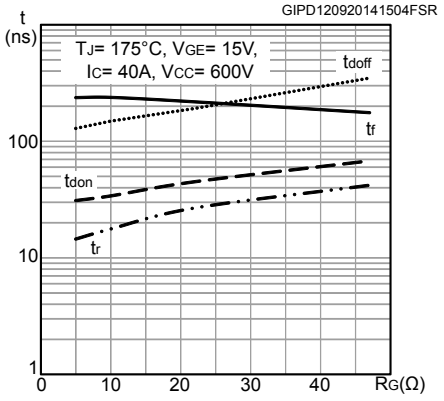


Figure 22. Reverse recovery current vs diode current slope

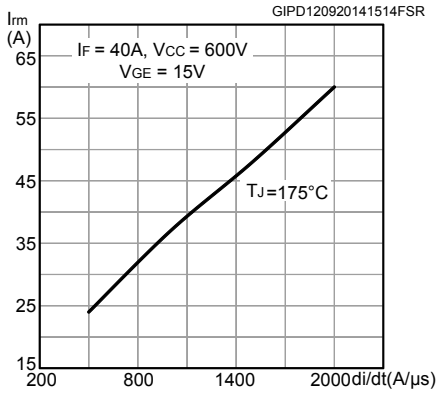


Figure 23. Reverse recovery time vs diode current slope

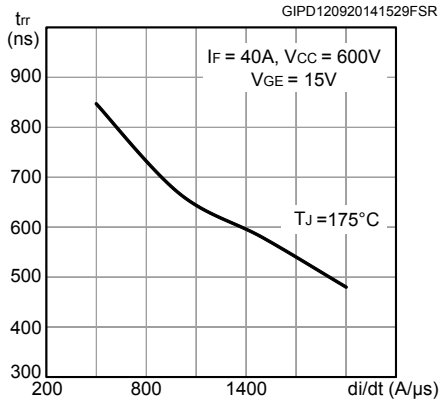


Figure 24. Reverse recovery charge vs diode current slope

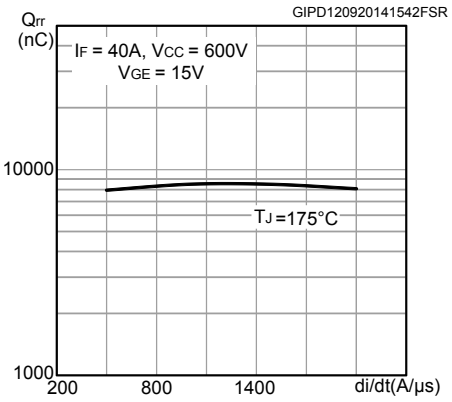


Figure 25. **Reverse recovery energy vs diode current slope**

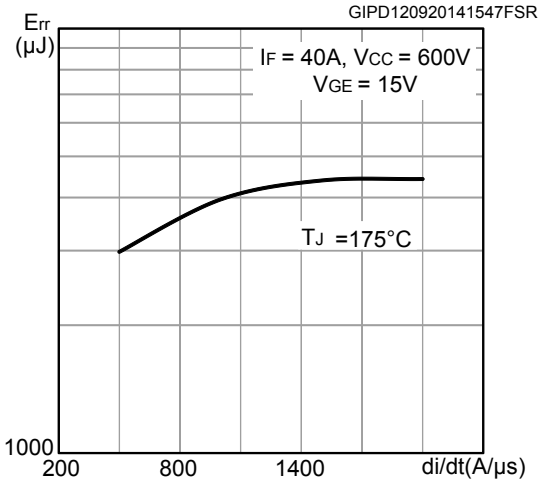


Figure 26. **Thermal impedance for IGBT**

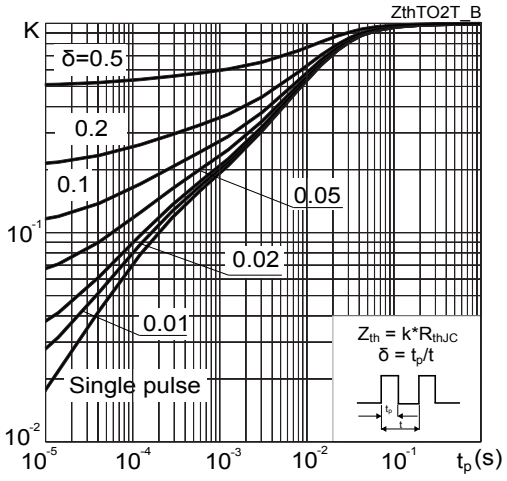
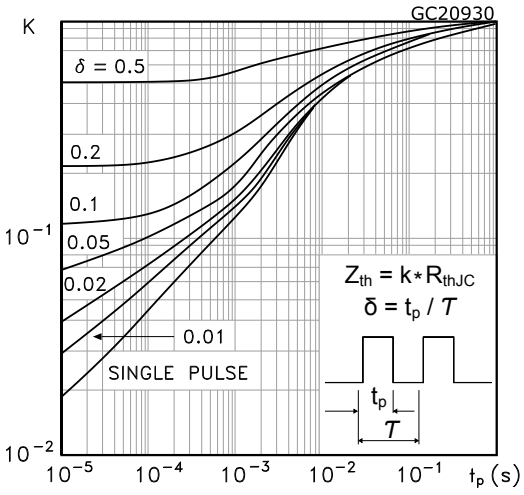


Figure 27. **Thermal impedance for diode**



3 Test circuits

Figure 28. Test circuit for inductive load switching

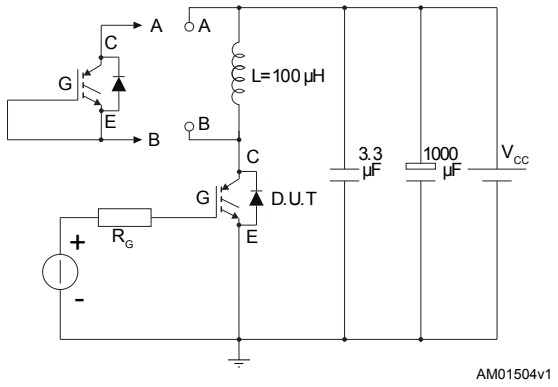


Figure 29. Gate charge test circuit

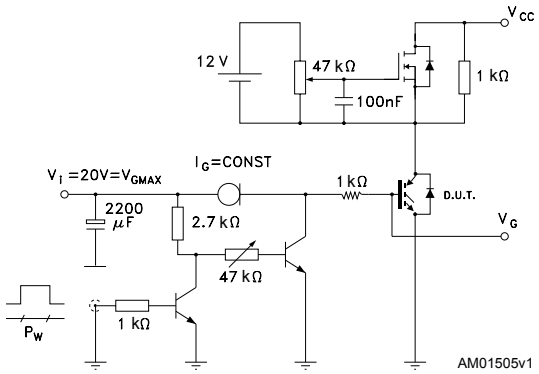


Figure 30. Switching waveform

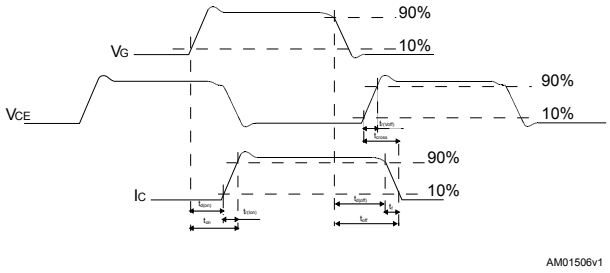
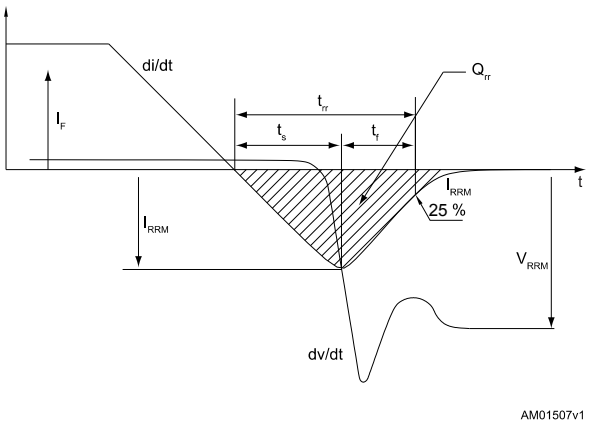


Figure 31. Diode reverse recovery waveform

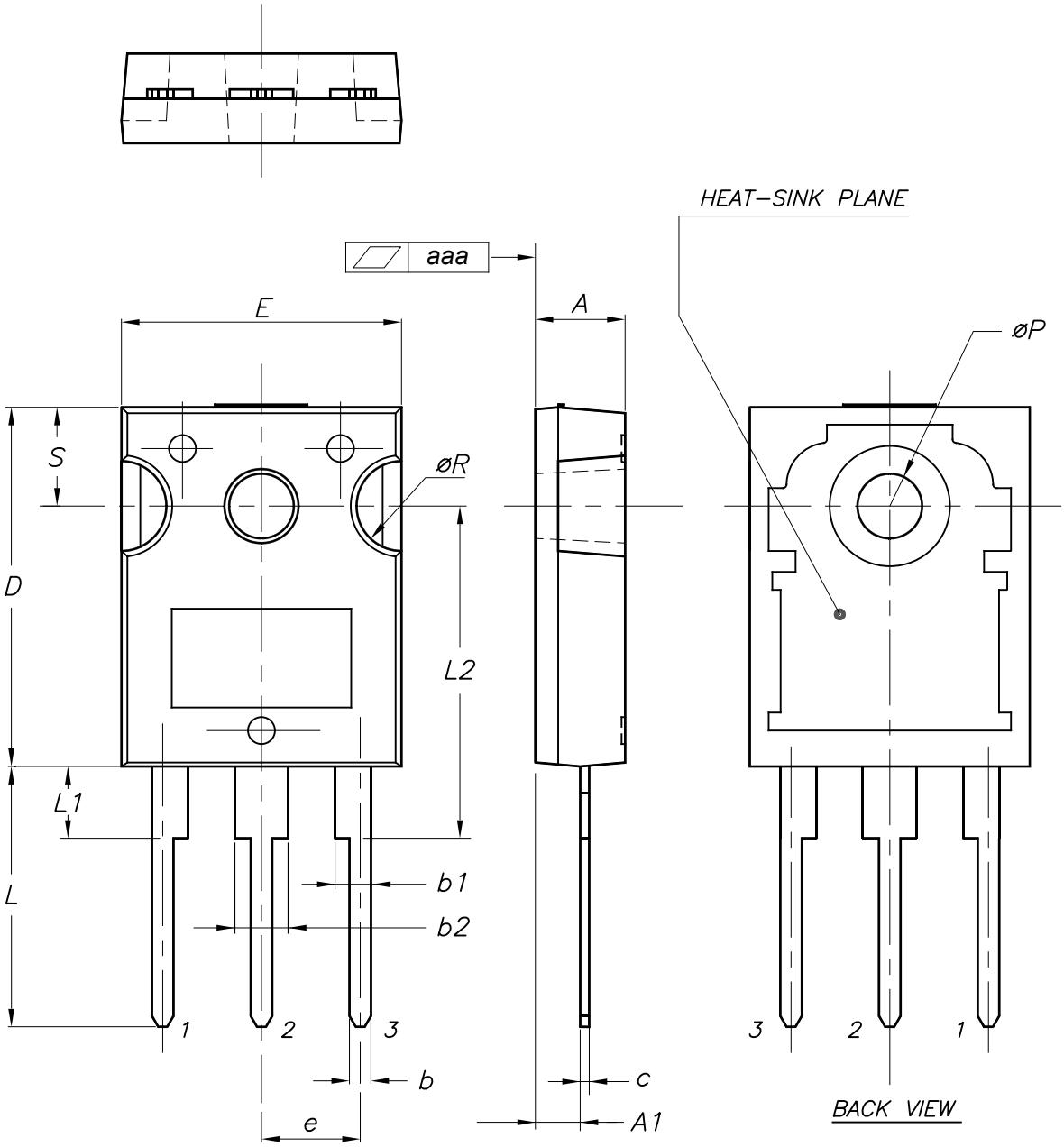


4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 32. TO-247 package outline



0075325_10

Table 7. **TO-247 package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70
aaa		0.04	0.10

4.2 TO-247 long leads package information

Figure 33. **TO-247 long leads package outline**

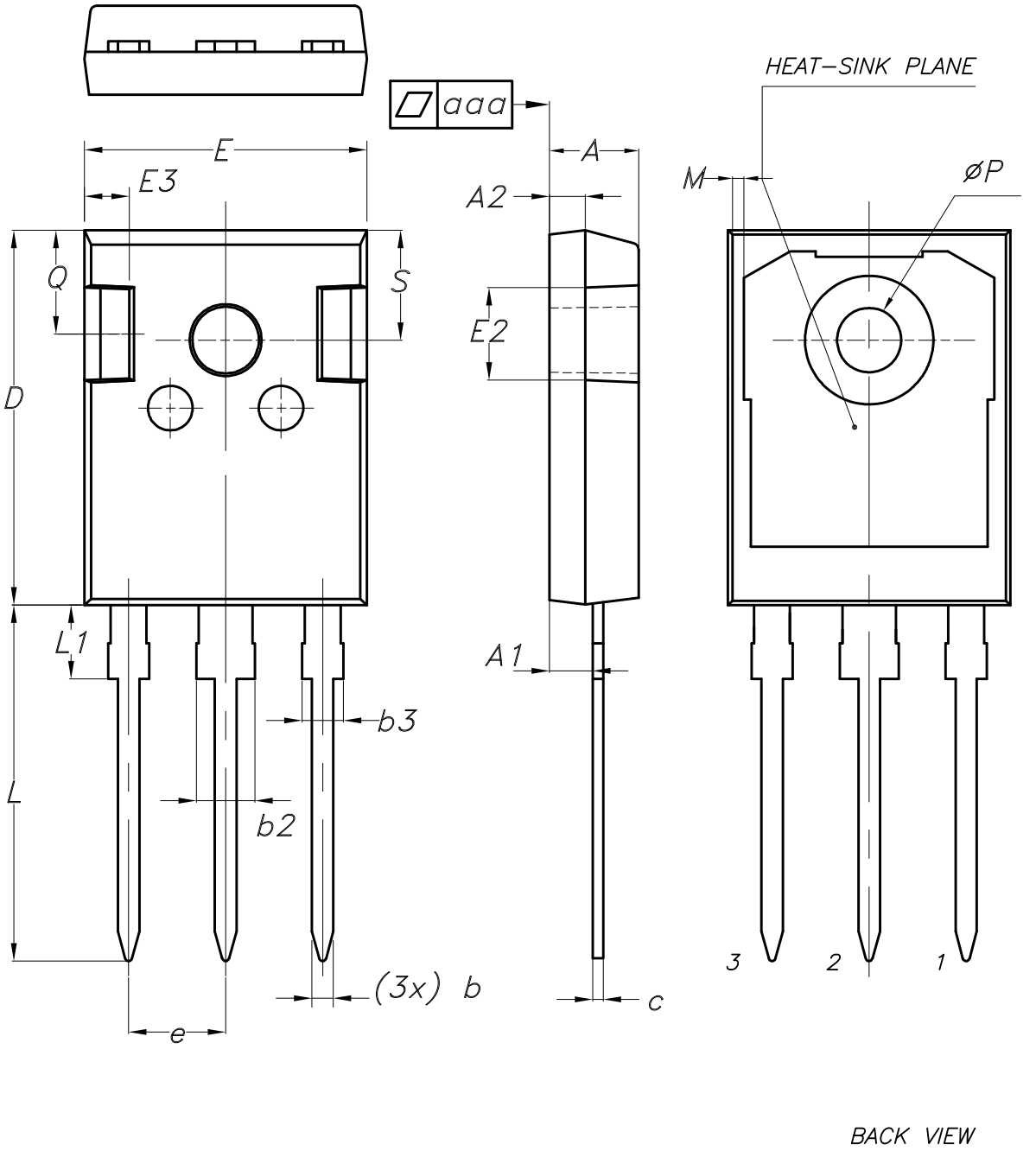


Table 8. **TO-247 long leads package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
M	0.35		0.95
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
22-Apr-2014	1	Initial release.
16-Sep-2014	2	Document status promoted from preliminary to production data. Added *Section 2.1: Electrical characteristics (curves)*.
10-Nov-2014	3	Updated VF value in *Table 4: Static characteristics* and *Figure 32: Diode recovery times waveform*. Minor text changes.
12-Feb-2025	4	Updated title in cover page. Updated Section 4.1: TO-247 package information, and Section 4.2: TO-247 long leads package information. Minor text changes.

Contents

1 **Electrical ratings** 2
2 **Electrical characteristics** 3
2.1 Electrical characteristics (curves) 5
3 **Test circuits** 10
4 **Package information** 11
4.1 TO-247 package information 11
4.2 TO-247 long leads package information 13
Revision history 15

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